

NEC**SILICON TRANSISTOR**
2SC3632-Z**NPN SILICON EPITAXIAL TRANSISTOR**
MP-3**DESCRIPTION**

2SC3632-Z is designed for High Voltage Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High Voltage $V_{CEO} = 600$ V
- High Speed $t_r < 0.5 \mu s$
- Complement to 2SA1413-Z

QUALITY GRADE

Standard

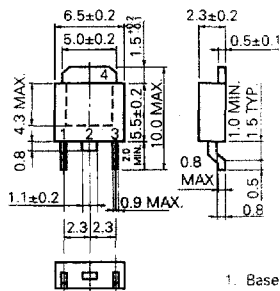
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Collector to Base Voltage	V_{CBO}	600	V
Collector to Emitter Voltage	V_{CEO}	600	V
Emitter to Base Voltage	V_{EB0}	7	V
Collector Current (DC)	I_C	1	A
Collector Current (Pulse)*	I_C	2	A
Total Power Dissipation ($T_a = 25^\circ C$)**	P_T	2.0	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10$ ms, Duty Cycle ≤ 50 %

** When mounted on ceramic substrate of $7.5 \text{ cm}^2 \times 0.7 \text{ mm}$

PACKAGE DIMENSIONS
(in millimeters)

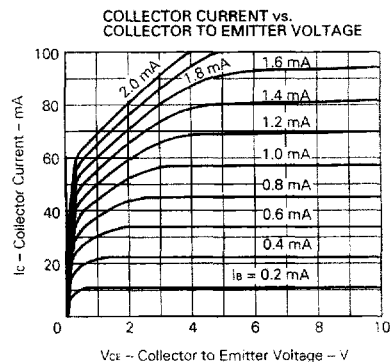
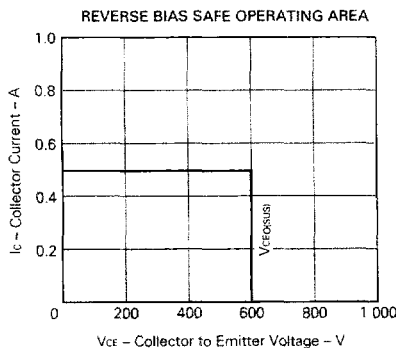
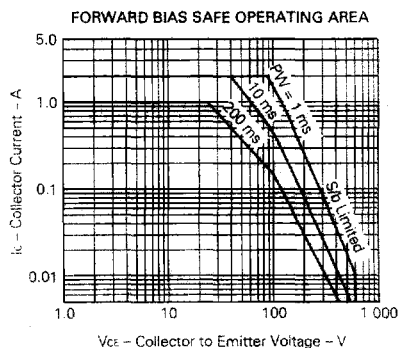
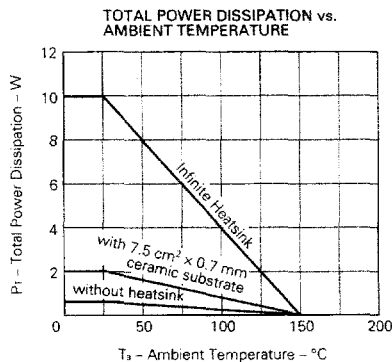
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			10	μA	$V_{CB} = 600\text{ V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}			10	μA	$V_{EB} = 7.0\text{ V}, I_C = 0$
DC Current Gain	h_{FE1}^*	30	55	120		$V_{CE} = 5.0\text{ V}, I_C = 100\text{ mA}$
DC Current Gain	h_{FE2}^*	5	7			$V_{CE} = 5.0\text{ V}, I_C = 500\text{ mA}$
Collector Saturation Voltage	$V_{CE(sat)}^*$		0.35	1.0	V	$I_C = 400\text{ mA}, I_B = 80\text{ mA}$
Base Saturation Voltage	$V_{BE(sat)}^*$		0.9	1.2	V	$I_C = 400\text{ mA}, I_B = 80\text{ mA}$
Gain Bandwidth Product	f_T		30		MHz	$V_{CE} = 5.0\text{ V}, I_E = -50\text{ mA}$
Output Capacitance	C_{ob}		14		pF	$V_{CB} = 10\text{ V}, I_E = 0, f = 1.0\text{ MHz}$
Turn-on Time	t_{on}		0.1	0.5	μs	$I_C = 0.5\text{ A}, R_L = 500\ \Omega$ $I_{B1} = -I_{B2} = 0.1\text{ A}$ $V_{CC} = 250\text{ V}$
Storage Time	t_{stg}		4.0	5.0	μs	
Fall Time	t_f		0.2	0.5	μs	

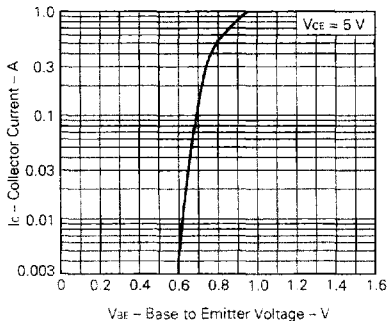
* Pulsed: $PW \leq 350\ \mu\text{s}$, Duty Cycle $\leq 2\%$

hFE Classification

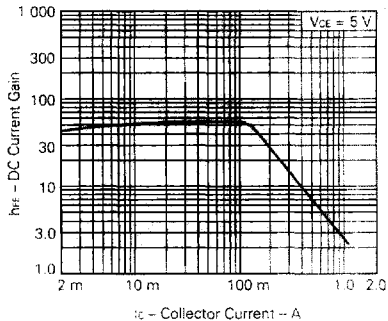
MARKING	M	L	K
h_{FE1}	30 to 60	40 to 80	60 to 120

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

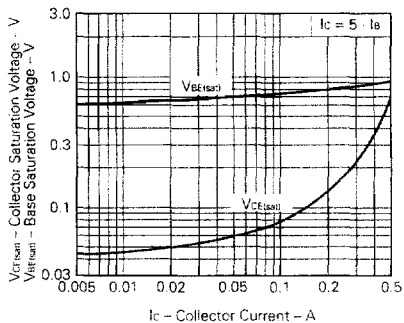
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



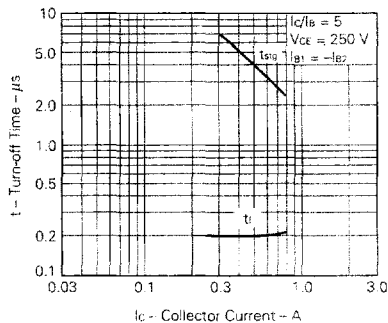
DC CURRENT GAIN vs.
COLLECTOR CURRENT



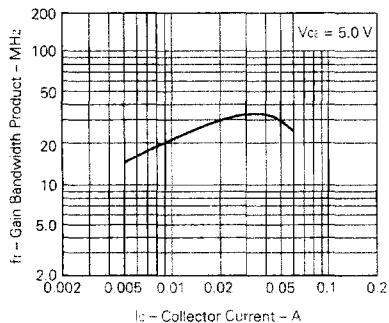
COLLECTOR AND BASE SATURATION
VOLTAGE vs. COLLECTOR CURRENT



TURN OFF TIME vs.
COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs.
COLLECTOR CURRENT



OUTPUT CAPACITANCE vs.
COLLECTOR TO BASE VOLTAGE

